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Team Nexperia



PBHV9040T

500 V, 0.25 A PNP high-voltage low V_{CEsat} (BISS) transistor Rev. 02 — 15 January 2009 Product data sh

Product data sheet

1. Product profile

1.1 General description

PNP high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8540T.

1.2 Features

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- AEC-Q101 qualified

1.3 Applications

- Electronic ballast for fluorescent lighting
- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch mode power supply

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-	-500	V
V_{CEO}	collector-emitter voltage	open base	-	-	-400	V
I _C	collector current		-	-	-0.25	Α
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V};$ $I_{C} = -50 \text{ mA}$	100	200	-	





2. Pinning information

Table 2. Pinning

I GIDIO E.	9		
Pin	Description	Simplified outline	Graphic symbol
1	base		_
2	emitter	3	3
3	collector	1 2	1 - 2
			sym013

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBHV9040T	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBHV9040T	W5*

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

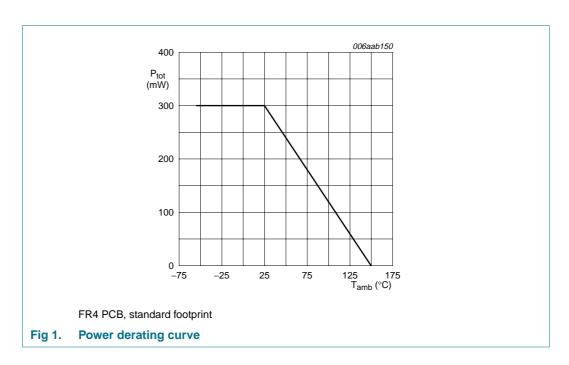
500 V, 0.25 A PNP high-voltage low V_{CEsat} (BISS) transistor

5. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-500	V
V_{CEO}	collector-emitter voltage	open base	-	-400	V
V _{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-500	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-0.25	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-0.5	Α
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u>	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		–55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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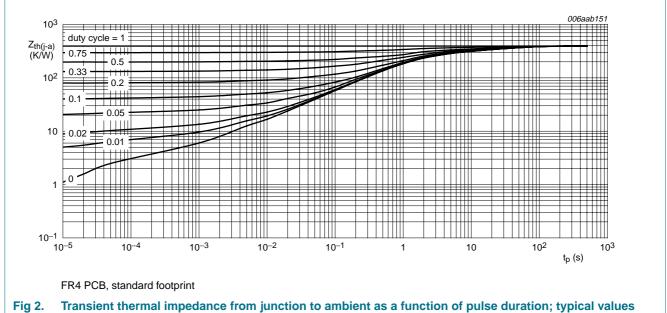
500 V, 0.25 A PNP high-voltage low V_{CEsat} (BISS) transistor

Thermal characteristics 6.

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	417	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	70	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



7. Characteristics

Table 7. Characteristics

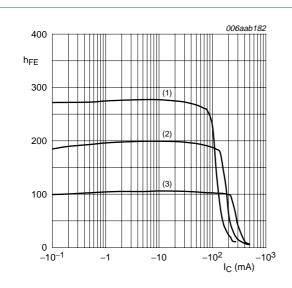
 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -320 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
	current	$V_{CB} = -320 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$		-	-	-10	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -320 \text{ V}; V_{BE} = 0 \text{ V}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; I_C = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V}$					
		$I_C = -50 \text{ mA}$		100	200	-	
		$I_C = -100 \text{ mA}$		80	200	-	
		$I_C = -250 \text{ mA}$	<u>[1]</u>	10	25	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -100 \text{ mA}; I_B = -20 \text{ mA}$		-	-110	-200	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -100 \text{ mA}; I_B = -20 \text{ mA}$	[1]	-	-1	-1.1	V
f _T	transition frequency	$V_{CE} = -10 \text{ V}; I_E = -10 \text{ mA};$ f = 100 MHz		-	55	-	MHz
C _c	collector capacitance	$V_{CB} = -20 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	7	-	pF
C _e	emitter capacitance	$V_{EB} = -0.5 \text{ V}; I_C = i_c = 0 \text{ A};$ f = 1 MHz		-	150	-	pF
t _d	delay time	$V_{CC} = -2 \text{ V}; I_C = -0.15 \text{ A};$		-	9	-	ns
t _r	rise time	$I_{Bon} = -0.03 \text{ A};$		-	1810	-	ns
t _{on}	turn-on time	$-I_{Boff} = 0.03 A$		-	1819	-	ns
ts	storage time			-	715	-	ns
t _f	fall time			-	1085	-	ns
t _{off}	turn-off time			-	1800	-	ns

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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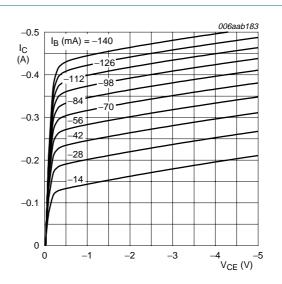




 $V_{CE} = -10 \text{ V}$

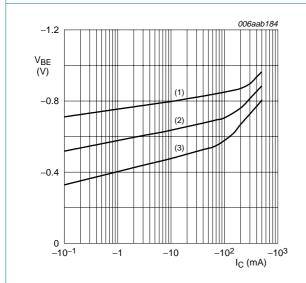
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \,^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

DC current gain as a function of collector Fig 3. current; typical values



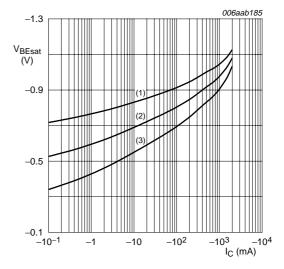
 $T_{amb} = 25 \, ^{\circ}C$

Collector current as a function of Fig 4. collector-emitter voltage; typical values



- $V_{CE} = -10 \text{ V}$
- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values

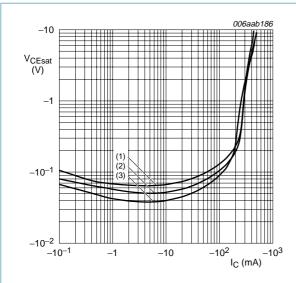


 $I_C/I_B = 5$

- (1) $T_{amb} = -55$ °C
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

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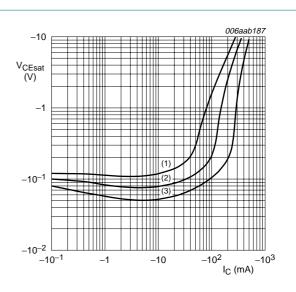
$$I_{\rm C}/I_{\rm B} = 5$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \,^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

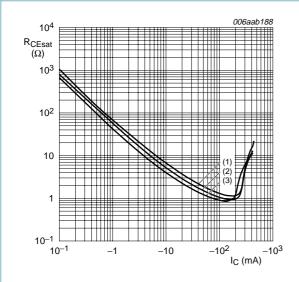


(1)
$$I_C/I_B = 20$$

(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



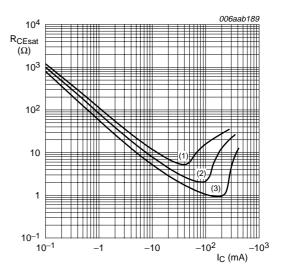
 $I_{\rm C}/I_{\rm B}=5$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 9. Collector-emitter saturation resistance as a function of collector current; typical values



T_{amb} = 25 °C

(1)
$$I_C/I_B = 20$$

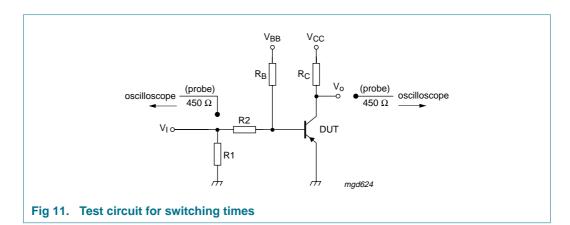
(2) $I_C/I_B = 10$

 $(3) \quad I_{C}/I_{B}=5$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

500 V, 0.25 A PNP high-voltage low V_{CEsat} (BISS) transistor

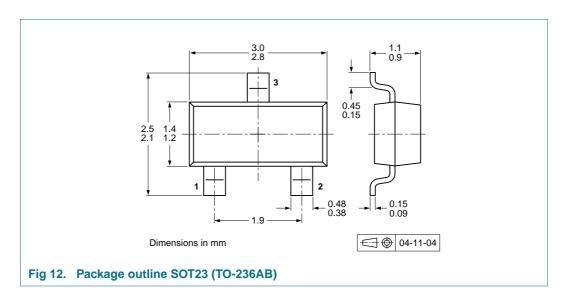
8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

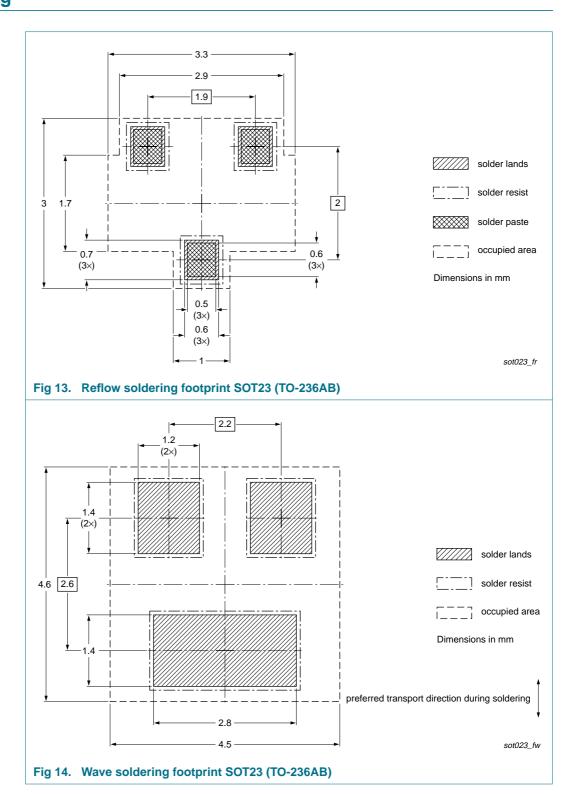
Type number	Package	Description	Packing quantity	
			3000	10000
PBHV9040T	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

^[1] For further information and the availability of packing methods, see Section 14.

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500 V, 0.25 A PNP high-voltage low V_{CEsat} (BISS) transistor

11. Soldering





12. Revision history

Table 9. Revision history

D ID	5.1	Data da atata	01	0
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9040T_2	20090115	Product data sheet	-	PBHV9040T_1
Modifications:	• Table 5: I _{BM} v	value changed from −100 mA t	to –200 mA	
	 <u>Table 7</u>: t_{off} v 	alue amended to 1800 ns		
	 Section 13 "L 	egal information": updated		
PBHV9040T_1	20080212	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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NXP Semiconductors

PBHV9040T

500 V, 0.25 A PNP high-voltage low V_{CEsat} (BISS) transistor

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